

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14094	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).CCLS.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/26 16:05
L2	0	1 and (source drain gate).clm. and ("Zn.sub.2" near1 "SnO.sub.4" spinel near1 (zinc adj stannate)).clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 16:07
L3	0	((hoffman near1 randy).in. (chiang near1 hai).in. (wager near1 john).in. (hewlett near1 packard).as.) and (source drain gate).clm. and ("Zn.sub.2" near1 "SnO.sub.4" spinel near1 (zinc adj stannate) ZTO).clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 16:09
L4	0	1 and (source drain gate).ti,ab,clm. and ("Zn.sub.2" near1 "SnO.sub.4" spinel near1 (zinc adj stannate)).ti,ab,clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 16:09
L5	0	1 and (source drain gate) and ("Zn.sub.2" near1 "SnO.sub.4" spinel near1 (zinc adj stannate)).ti,ab,clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 16:10
L6	0	1 and (source drain gate) and ((Zn.sub.2" near1 "SnO.sub.4") spinel near1 (zinc adj stannate)).ti,ab,clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 16:10
S1	3	("5,470,768") or ("5,879,973") or ("6,569,720").PN.	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2006/05/31 15:33

S2	20	((("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:48
S3	10	((("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550")).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:53
S4	1	("20030013261").PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:52
S5	11	S3 S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:53
S6	9	((("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462")).PN. or ((2002/0153587) or (2002/0171085)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:56
S7	11	((("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462") or ("20020153587") or ("20020171085")).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:57

S8	0	ep-0040076\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:58
S9	0	ep-00040076\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:59
S10	82	sasano.in.	EPO	OR	OFF	2005/10/01 17:02
S11	0	sasano.in. and drain and compound	EPO	OR	OFF	2005/10/01 17:01
S12	0	sasano.in. and drain	EPO	OR	OFF	2005/10/01 17:02
S13	4	sasano.in. and semiconductor	EPO	OR	OFF	2005/10/01 17:02
S14	1	(EP-40076-\$).did.	EPO	OR	OFF	2005/10/01 17:08
S15	4	(("5,744,864") or ("20020101557")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 17:08
S16	2	(("5,744,864") or ("20020101557")).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 17:08
S17	4	"763353".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:40
S18	4	"763353".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:42
S19	2	"20040127038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:51
S20	5	"2004023432".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:52

S21	2	"20040023432".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:53
S22	4	S19 S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:55
S23	2	jp-2003086808\$-.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:56
S24	2	("20030047785").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:56
S25	0	Garcia.in. and ("Zn.sub.2" near1 "Sn" near1 "O. sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 12:44
S26	0	("257"/\$7.ccls. "438"/\$7. ccls. "117"/\$7.ccls.) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:45
S27	3	("257"/\$7.ccls. "438"/\$7. ccls. "117"/\$7.ccls.) and (zinc adj stannate "Zn. sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:48
S28	10	(zinc adj stannate "Zn. sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:49
S29	2	(zinc adj stannate "Zn. sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:50

S30	0	(zinc adj stannate "Zn. sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:02
S31	0	(zinc adj stannate "Zn. sub.2" near1 "Sn" near1 "O.sub.4" cubic adj spinel) near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:02
S32	0	(zinc adj stannate "Zn. sub.2" near1 "Sn" near1 "O.sub.4" zinc adj spinel) near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:10
S33	324	transparent near1 (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:11
S34	0	(transparent near1 (thin adj film adj transistor tft) ttft) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 13:12
S35	0	((transparent near1 (thin adj film adj transistor tft) ttft) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 13:12
S36	0	alumin\$1um adj titanate near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 15:33

S37	9707	("AlO.sub."\$4 "TiO.sub."\$4 "Al.sub."\$4 alumin\$1um adj titanate titanium adj aluminate) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT)	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:58
S38	115	(("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT)	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:00
S39	79	(("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) and @ad< "20030726"	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:03
S40	0	(("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) near15 gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) and @ad< "20030726"	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:16
S41	4	"763353".ap.	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/01 11:39
S42	706	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O.sub."\$3)) "AlO.sub."\$3) near8 (titanium adj oxide ("Ti.sub."\$3 near1 (O "O.sub."\$3)) "TiO.sub."\$3) same gate	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:52

S43	131	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O. sub."\$3)) "AlO.sub."\$3) near8 (titanium adj oxide ("Ti.sub."\$3 near1 (O "O. sub."\$3)) "TiO.sub."\$3) near10 gate near10 (dielectric insulati\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:53
S44	66	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O. sub."\$3)) "AlO.sub."\$3) near8 (titanium adj oxide ("Ti.sub."\$3 near1 (O "O. sub."\$3)) "TiO.sub."\$3) near10 gate near10 (dielectric insulati\$2)	USPAT	OR	ON	2006/06/01 11:53
S45	2	"20050253157".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/01 15:47
S46	140	rf adj sputtering near6 amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/01 15:47
S47	0	(zno zinc adj oxide) near10 (rf adj sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:48
S48	16	(oxide) near10 (rf adj sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:50
S49	259	(oxide) near10 (sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:50
S50	19	(zinc adj oxide zno) near10 (sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:51
S51	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2006/06/01 16:10
S52	1	S51 and transparent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:10

S53	0	dissocation adj constant near5 (zinc adj stannate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:17
S54	0	dissocation adj constant near5 (( "Zn.sub.2" near1 "Sn" near1 "O.sub.4") (zinc adj stannate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:40
S55	0	(indium-tin-oxide indium adj tin adj oxide ITO) and "20040127038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:16
S56	11	drain-to-gate near4 bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:24
S57	1894	drain near2 connecti\$2 near2 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:25
S58	7956	drain near1 connecti\$3 near1 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:25
S59	571	drain near1 connecti\$3 near1 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:33
S60	49	back adj gate and gate-to-drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:34
S61	2	back adj gate and gate-to-drain and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:35
S62	2	back adj gate and gate-to-drain and (otft tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:35

S63	2	(back adj gate back-gate) and gate-to-drain and (otft tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:36
S64	334	(back adj gate back-gate) and (otft tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:36
S65	267	(back adj gate back-gate) and (otft tft thin adj film adj transistor) and circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:02
S66	29	hot adj electron.ti,ab,clm. and gate-to-drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:05
S67	585	hot adj electron.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:11
S68	40	hot adj electron adj effect. ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:14
S69	18	hot adj electron adj effect. ti. and gate near5 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:15
S70	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2006/06/02 08:40
S71	0	S70 and means	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 08:41
S72	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2006/06/02 08:41
S73	0	S70 and "means"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 08:41

S74	524	(thin adj film adj transistor tft).ti,ab,clm. and (indium-tin ITO) near8 source and (indium-tin ITO) near8 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 09:41
S75	54	(thin adj film adj transistor tft).ti,ab,clm. and (indium-tin ITO) near2 source and (indium-tin ITO) near2 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 09:41
S76	41	(US-20050104508-\$ or US-20040066484-\$ or US-20030185266-\$ or US-20050017244-\$ or US-20030207502-\$ or US-20030224550-\$ or US-20030219530-\$ or US-20030218222-\$ or US-20030218221-\$ or US-20030186489-\$ or US-20030139026-\$ or US-20030104659-\$ or US-20030180996-\$ or US-20030013261-\$ or US-20020171085-\$ or US-20020153587-\$ or US-20040127038-\$ or US-20040023432-\$ or US-20030047785-\$).did. or (US-4521698-\$ or US-6569720-\$ or US-6561174-\$ or US-6391462-\$ or US-6362499-\$ or US-5744864-\$ or US-5107314-\$ or US-4887255-\$ or US-4589026-\$ or US-5879973-\$ or US-5470768-\$ or US-6255655-\$ or US-6255130-\$ or US-4559238-\$ or US-6653206-\$ or US-6617609-\$ or US-7017830-\$).did. or (EP-40076-\$).did. or (JP-2003086808-\$).did. or (WO-200217368-\$ or WO-2004034449-\$ or US-20030047785-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/06/02 10:16

S77	0	(( "TiO.sub."\$4 near4 "AlO. sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) near15 gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) and @ad< "20030726" and S76	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:17
S78	0	("AlO.sub."\$3 "A.sub.2O. sub.3") near10 ("TiO. sub."S72 "TiO.sub.2") near10 ((insulati\$2 (dielectric) near2 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:25
S79	69580	("Al.sub."\$1 near1 "O. sub."\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:26
S80	0	("Al.sub."\$1 near1 "O. sub."\$1) near20 ("Ti. sub."\$1 near1 "O.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination multi- layer\$2 multilayer\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:28
S81	0	("Al.sub."\$1 near1 "O. sub."\$1) near20 ("Ti. sub."\$1 near1 "O.sub."\$1) near20 gate near20 (dielectric insulati\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:28
S82	87	(( "Al.sub."\$1 near1 "O. sub."\$1) "AlO.sub."\$1) near20 (( "Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:30
S83	0	(( "Al.sub."\$1 near1 "O. sub."\$1) "AlO.sub."\$1) near20 (( "Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 mixture	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:30
S84	1	(( "Al.sub."\$1 near1 "O. sub."\$1) "AlO.sub."\$1) near20 (( "Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 mixture	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:35

S85	9	(( "Al.sub."\$1 near1 "O. sub."\$1) "AlO.sub."\$1) near20 (( "Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:42
S86	0	(( "Al.sub."\$1 near1 "O. sub."\$1) "AlO.sub."\$1) near20 (( "Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer) and (thin adj film adj transistor tft otft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:43
S87	9	(( "Al.sub."\$1 near1 "O. sub."\$1) "AlO.sub."\$1) near20 (( "Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:53
S88	9	(( "Al.sub."\$1 near1 "O. sub."\$1) "AlO.sub."\$1 (alumin\$1um adj titanate) (titanium adj aluminate)) near20 (( "Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:55
S89	9	(( "Al.sub."\$3 near1 "O. sub."\$3) "AlO.sub."\$3 (alumin\$1um adj titanate) (titanium adj aluminate)) near20 (( "Ti.sub."\$3 near1 "O.sub."\$3) "TiO.sub."\$3) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:48
S90	209	(( "Al.sub."\$3 near1 "O. sub."\$3) "AlO.sub."\$3) near20 (( "Ti.sub."\$3 near1 "O.sub."\$3) "TiO.sub."\$3) near20 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:49

S91	5	(( "Al.sub."\$3 near1 "O. sub."\$3) "AlO.sub."\$3) near20 (( "Ti.sub."\$3 near1 "O.sub."\$3) "TiO.sub."\$3) near20 barrier near20 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:52
S92	0	(( "Al.sub."\$3 near1 "O. sub."\$3) "AlO.sub."\$3) near20 (cap adj (layer film)) near20 gate near20 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:53
S93	3	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O. sub."\$3) "AlO.sub."\$3) near8 (cap adj layer) near20 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:59
S94	1839	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O. sub."\$3) "AlO.sub."\$3) near4 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:59
S95	45	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O. sub."\$3) "AlO.sub."\$3) near4 barrier near4 (Ti titanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 13:03
S96	27	((alumin\$1um adj oxide) ("Al.sub."\$3 near1 (O "O. sub."\$3) "AlO.sub."\$3) near4 barrier near4 (Ti titanium) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 13:03
S97	11320	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 14:32
S98	0	S97 and ((alumin\$1um adj titinate) (titanium adj aluminate) ("Al.sub."\$2 near1 "O.sub."\$2 "AlO. sub."\$2 alumin\$1um adj oxide)) near20 ("Ti. sub."\$2 near1 "O.sub."\$2 near1 "TiO.sub."\$2 (titanium adj oxide)) near20 gate and (channel semiconductor) near4 (("Zn.sub."\$2 near1 "SnO. sub."\$2) ("Zn.sub."\$2 near1 "O") near10 ("SnO.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 14:47

		sub."\$2)))				
S99	8	(("6836540") or ("6998656") or ("6940097") or ("7026713")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 14:49
S100	45	randy near1 hoffman.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 14:49
S101	26	randy near1 hoffman.in. and (zinc adj oxide ZnO ("Zn.sub.2" near1 "O")) and (Ti titanium) and (Al alumin\$1um)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 14:51
S102	89	(hewlett.as. hoffman.in. (hai near1 chiang).in. (john near2 wager).in.) and (zinc tin) adj oxide.ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 11:09
S103	2	(hewlett.as. hoffman.in. (hai near1 chiang).in. (john near2 wager).in.) and (zinc tin) adj oxide.ti, ab,clm. and stannate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 11:10
S104	18	(hewlett.as. hoffman.in. (hai near1 chiang).in. (john near2 wager).in.) and (zinc tin) adj oxide.ti, ab,clm. and (stannate "SnO.sub."\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 11:10
S105	2	"20040127038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/14 12:05
S106	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2007/11/14 15:31
S107	0	(US-20050017244-\$).did. and means	US-PGPUB	OR	ON	2007/11/14 15:31
S108	1743	(aluminum adj oxide) and strontium adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/14 19:15
S109	7	"410830".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/15 10:27

S110	2	("20040127038").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 13:26
S111	0	("533453.ap.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 14:15
S112	2	("20020172317").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 14:18
S113	2	("4093886").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 14:53
S114	0	wo-9108180\$-\$did.	USPAT	OR	OFF	2007/11/15 14:54
S115	2	wo-9108180\$-\$did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 16:23
S116	32	percentage near3 porosity near3 "%"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/15 16:24
S122	2	"20040127038".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:03
S123	2	"4521698".PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:05

S124	2	"6674495".PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:05
S125	13	"6100558"	USPAT	OR	OFF	2007/11/21 10:50
S126	1	("6100558").PN.	USPAT; USOCR	OR	OFF	2007/11/21 10:52
S127	2	("20040169210").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:53
S128	2	("6184946").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:53
S129	0	("20060183274").PN.	USPAT; USOCR	OR	OFF	2007/11/22 08:36
S130	9	carcia.in. and thin adj film adj transistor	US-PGPUB; USPAT	OR	ON	2007/11/22 08:44
S131	6	thin adj film adj transistor and (zinc-tin adj oxide zto) near4 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:49
S132	7	(tft thin adj film adj transistor) and (zinc-tin adj oxide zto) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:50
S133	11	(tft thin adj film adj transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:52
S134	12	(tft thin adj film adj transistor mos mosfet) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:53

S135	10	(mos mosfet) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:53
S136	11	(mosfet transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:56
S137	11	(mosfet transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide "zno:sn") near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:03
S138	0	("20050017244").PN.	USPAT; USOCR	OR	OFF	2007/11/22 09:03
S139	2	("20050017244").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/22 09:06
S140	2	"20060284171"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/22 09:11
S141	10	zinc near1 tin near1 oxide near10 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/22 09:12
S142	2	zinc near1 tin near1 oxide near10 channel not hoffman.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:32
S143	12023	zinc near2 tin near2 oxide zto zto "zno:sn" "sno"\$3"zn"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:33

S144	26	(zinc near2 tin near2 oxide zito zto "zno:sn" "sno"\$3"zn") near4 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:44
S145	0	zno near4 sno\$1 near4 (mixture combination) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:45
S146	0	zno near4 sno\$1 near8 (mixture combination) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:45
S147	5	(zinc adj oxide zno) near4 (tin adj oxide sno\$1) near8 (mixture combination) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:50
S148	31	(zinc adj oxide zno) near4 (tin adj oxide sno\$1) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:59
S149	1	(zinc-tin- adj oxide zinc adj tin adj oxide) near20 channel.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:03
S150	2	"20040023432".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:07
S151	2	jp-2003088808\$-.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:10

S152	0	ohtomo.in. and zto	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:11
S153	0	ohtomo.in. and (zinc-tin-oxide zto)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:11
S154	0	(ohtomo.in. kawasaki.in.) and (zinc-tin-oxide zto)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:17
S155	23	"5470788"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:18
S156	3	(("5470788") or ("5879973") or ("6569720")).PN.	USPAT; USOCR	OR	OFF	2007/11/22 10:24
S157	3	((("5470768") or ("5879973") or ("6569720"))).PN.	USPAT; USOCR	OR	OFF	2007/11/22 10:30
S158	11	((("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462") or ("20020153587") or ("20020171085"))).PN.	US-PGPUB; USPAT	OR	OFF	2007/11/22 10:31
S159	2	("20040127038").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 13:10
S160	13987	"SnO.sub.2"	USPAT	OR	OFF	2007/11/23 07:02
S161	0	"SnO.sub.2" near10 "ZnO" near10 (combination mixture) near20 channel and transistor	USPAT	OR	ON	2007/11/23 07:03

S162	4	"SnO.sub.2" near10 "ZnO" near10 (combination mixture) same channel and transistor	USPAT	OR	ON	2007/11/23 08:41
S163	2	jp-60198861\$-\$-did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 08:41
S164	1214	sputtering near4 ("SnO. sub.2" "ZnO")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 13:11
S165	211	sputtering near4 ("SnO. sub.2" "ZnO") and channel and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 13:11
S166	4	sputtering near4 ("SnO. sub.2" "ZnO") and channel and semiconductor and (Garcia.in. Gillessen.in.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 13:55
S167	1	("6,100,558").PN.	USPAT; USOCR	OR	OFF	2007/11/23 14:41
S168	13512	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 14:42
S169	6	S168 and (thin adj film adj transistor tft) and (zinc-tin-oxide Zn-Sn-oxide (ZnO near10 "SnO.sub.2") ("Zn. sub.2" near1 "SnO.sub.4") zinc adj stann?te "ZnSnO. sub.3") near20 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 14:46

S170	3	((randy near2 hoffman).in. (hai near2 chiang).in. (john near2 wager).in. hewlett.as. oregon.as.) and (thin adj film adj transistor tft).clm. and (zinc-tin-oxide Zn-Sn-oxide (ZnO near10 "SnO.sub.2") ("Zn.sub.2" near1 "SnO. sub.4") zinc adj stann?te "ZnSnO.sub.3") near20 channel.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 14:48
S171	2	"20040127038".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 09:46
S172	423	non-stoichiometric adj compound	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 10:53
S173	2	"2003185266".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 14:01
S174	2	"20030185266".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 14:02
S175	1	"20030185266".pn. and (sputter sputtering)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 14:03
S176	0	sputtering near10 amorphous near10 zinc-tin-oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:05
S177	0	sputtering near10 crystalline near10 zinc-tin-oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:05

S178	0	sputtering near10 crystal near10 zinc-tin-ozide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:05
S179	4961	sputtering near10 crystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:05
S180	2624	sputtering near5 crystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:06
S181	632	method near5 sputtering near5 crystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:06
S182	188	method near5 sputtering near5 crystal.ti,ab,clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/08 16:06
S183	2	"20040169791"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 15:29
S184	0	S183 and intermittent	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 15:31
S185	0	S183 and blocking adj material	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 15:31

S186	0	S183 and blocking	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 15:35
S187	1	S183 and block	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 15:35
S188	6	(zinc adj tin adj oxide zinc-tin-oxide ZTO) near3 amorphous same channel and (tft ttft thin adj film adj tranistsor transistor mosfet channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:15
S189	6	(zinc adj tin adj oxide zinc-tin-oxide ZTO) near3 amorphous and (tft ttft thin adj film adj transistor transistor mosfet channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:17
S190	8	(zinc adj tin adj oxide zinc-tin-oxide ZTO ilmenite cubic adj spinel) near3 amorphous and (tft ttft thin adj film adj transistor transistor mosfet channel)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:21
S191	6	ternary adj compound near4 sputtering	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:25
S192	1	ternary adj compound near4 sputtering same amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:25
S193	3	("SnO.sub.2" near4 "ZnO") near4 sputtering same amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:26

S194	0	("SnO.sub.2" near4 "ZnO") near4 sputtering same crystalline	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:48
S195	0	("SnO.sub.2" near4 "ZnO") near4 sputtering same crystallinity	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:49
S196	0	("SnO.sub.2" near4 "ZnO") near4 sputtering same polycrystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:49
S197	0	("SnO.sub.2" near4 "ZnO") near4 sputtering same polycrystalline	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:49
S198	2	"20030185266".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:50
S199	2	"20040127038".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:53
S200	0	magnetron adj sputtering near4 amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:55
S201	139	magnetron adj sputtering near4 amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 17:55

S202	0	magnetron adj sputtering near4 amorphous near4 (ZnO "SnO. <sub>sub.2</sub> " zinc-tin-oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 18:02
S203	0	magnetron adj sputtering near4 amorphous near4 (ZnO "SnO. <sub>sub.2</sub> " zinc-tin-oxide ternary adj compound)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 18:02
S204	1	magnetron adj sputtering near4 amorphous near4 (ZnO "SnO. <sub>sub.2</sub> " zinc-tin-oxide ternary adj compound ZTO ITO)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/09 18:03
S205	0	mobility near3 (zinc adj stannate "Zn. <sub>sub.2</sub> ">\$1 near1 "SnO. <sub>sub.4</sub> ")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 11:47
S206	0	mobility near3 (zinc adj stannate ("Zn. <sub>sub.2</sub> ">\$1 near1 "SnO. <sub>sub.4</sub> "))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 11:47
S207	0	mobility near4 (zinc adj stannate ("Zn. <sub>sub.2</sub> ">\$1 near1 "SnO. <sub>sub.4</sub> "))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 11:48
S208	0	mobility near8 (zinc adj stannate ("Zn. <sub>sub.2</sub> ">\$1 near1 "SnO. <sub>sub.4</sub> "))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 11:48
S209	3	"20040127038"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/26 13:45

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